

Radiation Hardened Octal Three-State Buffer/Line Driver

Intersil's Satellite Applications FlowTM (SAF) devices are fully tested and guaranteed to 100kRAD total dose. These QML Class T devices are processed to a standard flow intended to meet the cost and shorter lead-time needs of large volume satellite manufacturers, while maintaining a high level of reliability.

The Intersil ACTS541T is a Radiation Hardened Octal Buffer/Line Driver, with three-state outputs. The output enable pins OE1, OE2 control the three-state outputs. If either enable is high the output will be in a high impedance state. For data output both enables must be low.

Specifications

Specifications for Rad Hard QML devices are controlled by the Defense Supply Center in Columbus (DSCC). The SMD numbers listed below must be used when ordering.

Detailed Electrical Specifications for the ACTS541T are contained in SMD 5962-96726. For more information, visit our website at:

www.intersil.com/

Intersil's Quality Management Plan (QM Plan), listing all Class T screening operations, is also available on our website.

www.intersil.com/

Ordering Information

ORDERING NUMBER	PART NUMBER	TEMP. RANGE (°C)
5962R9672602TRC	ACTS541DTR-02	-55 to 125
5962R9672602TXC	ACTS541KTR-02	-55 to 125

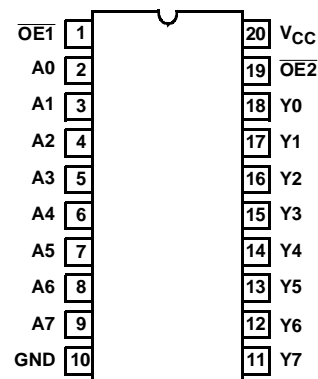
NOTE: **Minimum order quantity for -T is 150 units through distribution, or 450 units direct.**

Features

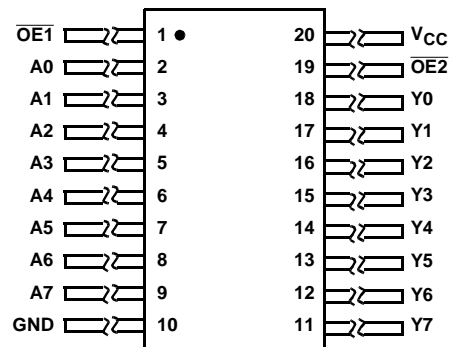
- QML Class T, Per MIL-PRF-38535
- Radiation Performance
 - Gamma Dose (γ) 1 x 10⁵ RAD(Si)
 - Latch-Up Free Under Any Conditions
 - Single Event Upset (SEU) Immunity: <1 x 10⁻¹⁰ Errors/Bit/Day (Typ)
 - SEU LET Threshold >100 MEV-cm²/mg
- 1.25 Micron Radiation Hardened SOS CMOS
- Significant Power Reduction Compared to ALSTTL Logic
- DC Operating Voltage Range 4.5V to 5.5V
- Input Logic Levels
 - V_{IL} = 0.8V Max
 - V_{IH} = V_{CC}/2 Min
- Fast Propagation Delay 21ns (Max), 14ns (Typ)

Pinouts

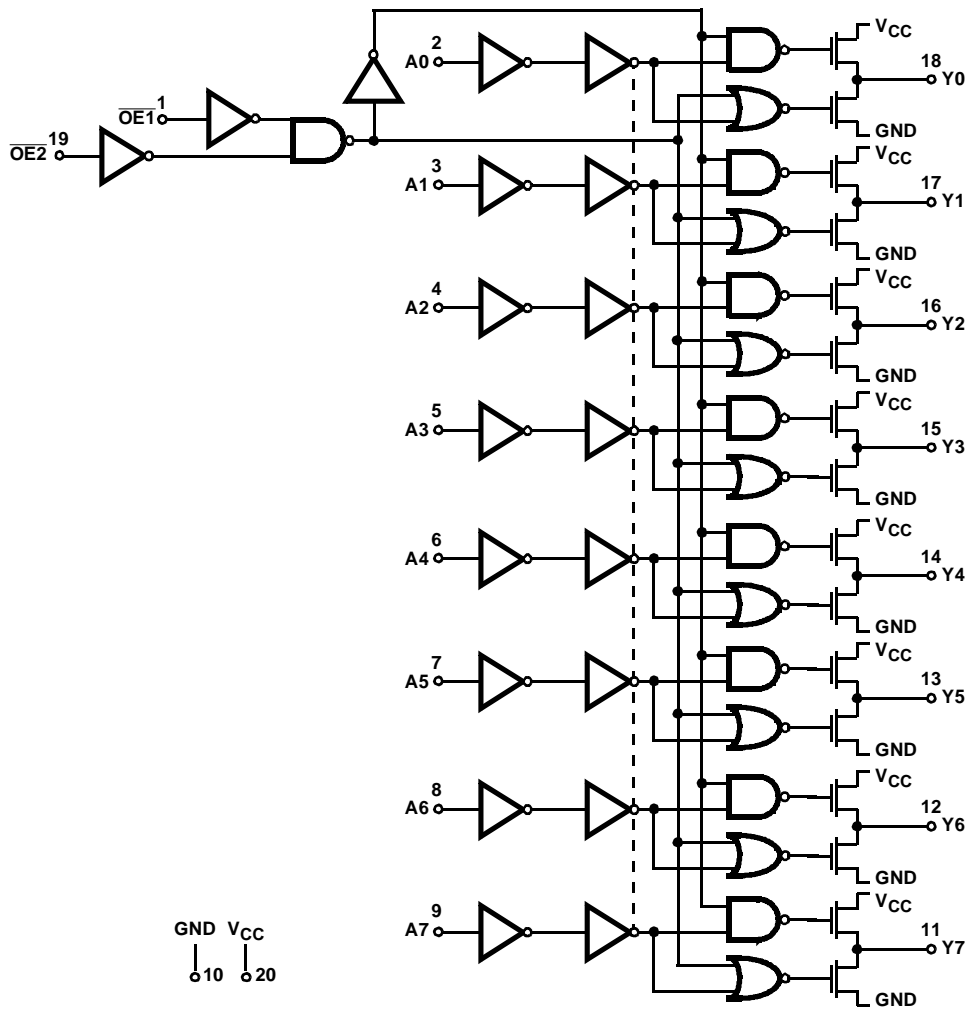
**ACTS541T (SBDIP), CDIP2-T20
TOP VIEW**



**ACTS541T (FLATPACK), CDFP4-F20
TOP VIEW**



Functional Diagram



TRUTH TABLE

INPUTS			OUTPUTS
$\overline{OE1}$	$\overline{OE2}$	A_n	Y_n
L	L	H	H
L	L	L	L
H	X	X	Z
X	H	X	Z

NOTE: L = Low Logic Level, H = High Logic Level, Z = High Impedance.

Die Characteristics

DIE DIMENSIONS:

(2600µm x 2600µm x 533µm ±51µm)
 102 x 102 x 21mils ±2mil

METALLIZATION:

Type: Al Si Cu
 Thickness: 10.0kÅ ±2kÅ

SUBSTRATE POTENTIAL:

Unbiased (Silicon on Sapphire)
 Bond Pad #20 (V_{CC}) First

BACKSIDE FINISH:

Sapphire

PASSIVATION:

Type: Silox (SiO₂)
 Thickness: 8.0kÅ ±1.0kÅ

WORST CASE CURRENT DENSITY:

< 2.0e5 A/cm²

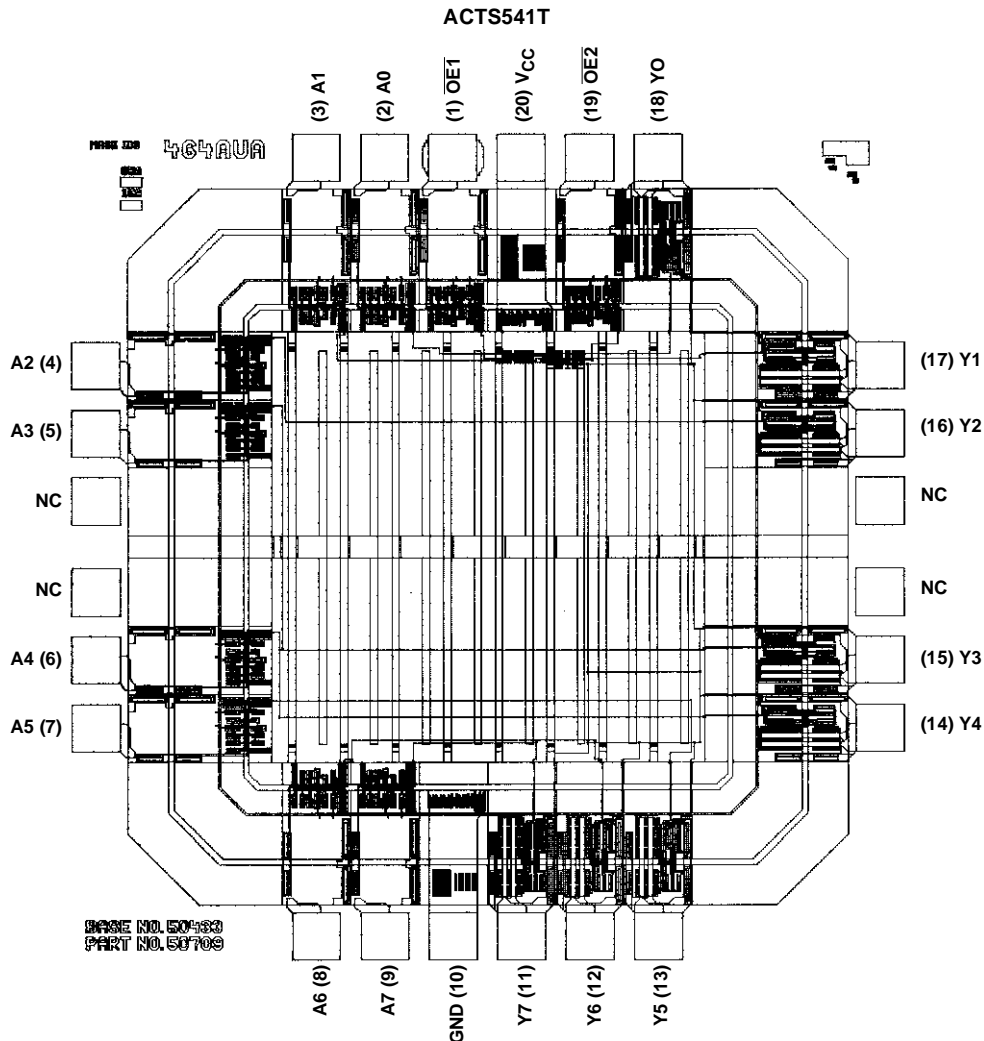
TRANSISTOR COUNT:

182

PROCESS:

CMOS SOS

Metalization Mask Layout



All Intersil U.S. products are manufactured, assembled and tested utilizing ISO9000 quality systems.
 Intersil Corporation's quality certifications can be viewed at www.intersil.com/design/quality

Intersil products are sold by description only. Intersil Corporation reserves the right to make changes in circuit design, software and/or specifications at any time without notice. Accordingly, the reader is cautioned to verify that data sheets are current before placing orders. Information furnished by Intersil is believed to be accurate and reliable. However, no responsibility is assumed by Intersil or its subsidiaries for its use, nor for any infringements of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of Intersil or its subsidiaries.

For information regarding Intersil Corporation and its products, see www.intersil.com